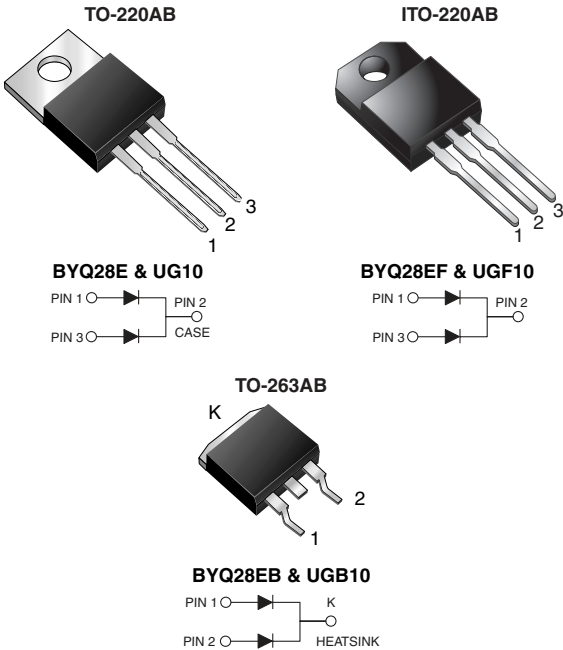


Dual Common Cathode Ultrafast Rectifier



FEATURES

- Glass passivated chip junction
- Ultrafast recovery times
- Soft recovery characteristics
- Low switching losses, high efficiency
- High forward surge capability
- Meets MSL level 1, per J-STD-020C, LF maximum peak of 245 °C (for TO-263AB package)
- Solder dip 260 °C, 40 s (for TO-220AB and ITO-220AB package)
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



TYPICAL APPLICATIONS

For use in low voltage, high frequency rectifier of switching power supplies, freewheeling diodes, dc-to-dc converters and polarity protection application.

MECHANICAL DATA

Case: TO-220AB, ITO-220AB, TO-263AB

Epoxy meets UL 94V-0 flammability rating

Terminals: Matte tin plated leads, solderable per J-STD-002B and JESD22-B102D

E3 suffix for commercial grade, meets JESD 201 class 1A whisker test, HE3 suffix for high reliability grade (AEC Q101 qualified), meets JESD 201 class 2 whisker test

Polarity: As marked

Mounting Torque: 10 in-lbs maximum

PRIMARY CHARACTERISTICS

$I_{F(AV)}$	5 A x 2
V_{RRM}	100 V, 150 V, 200 V
I_{FSM}	55 A
t_{rr}	25 ns
V_F	0.895 V
T_J max.	150 °C

MAXIMUM RATINGS ($T_C = 25$ °C unless otherwise noted)

PARAMETER	SYMBOL	UG10BCT	UG10CCT	UG10DCT	UNIT
		BYQ28E-100	BYQ28E-150	BYQ28E-200	
Maximum repetitive peak reverse voltage	V_{RRM}	100	150	200	V
Working peak reverse voltage	V_{RWM}	100	150	200	V
Maximum DC blocking voltage	V_{DC}	100	150	200	V
Maximum average forward rectified current at $T_C = 100$ °C total device per diode	$I_{F(AV)}$	10 5			A
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load per diode	I_{FSM}	55			A
Non-repetitive peak reverse current per diode at $t_p = 100$ μs	I_{RSM}	0.2			A
Electrostatic discharge capacitor voltage, human body model: C = 250 pF, R = 1.5 kΩ	V_C	8			kV
Operating junction and storage temperature range	T_J, T_{STG}	- 40 to + 150			°C
Isolation voltage (ITO-220AB only) from terminal to heatsink $t = 1$ min	V_{AC}	1500			V

BYQ28E(F,B)-100 thru BYQ28E(F,B)-200, UG(F,B)10BCT

Vishay General Semiconductor



ELECTRICAL CHARACTERISTICS ($T_C = 25\text{ }^\circ\text{C}$ unless otherwise noted)					
PARAMETER	TEST CONDITIONS		SYMBOL	VALUE	UNIT
Maximum instantaneous forward voltage per diode ⁽¹⁾	$I_F = 10\text{ A}$	$T_J = 25\text{ }^\circ\text{C}$	V_F	1.25	V
	$I_F = 5\text{ A}$	$T_J = 25\text{ }^\circ\text{C}$		1.10	
	$I_F = 5\text{ A}$	$T_J = 150\text{ }^\circ\text{C}$		0.895	
Maximum reverse current per diode at working peak reverse voltage		$T_J = 25\text{ }^\circ\text{C}$ $T_J = 100\text{ }^\circ\text{C}$	I_R	10 200	μA
Maximum reverse recovery time per diode	$I_F = 1.0\text{ A}$, $dI/dt = 100\text{ A}/\mu\text{s}$, $V_R = 30\text{ V}$, $I_{rr} = 0.1 I_{RM}$		t_{rr}	25	ns
Maximum reverse recovery time per diode	$I_F = 0.5\text{ A}$, $I_R = 1.0\text{ A}$, $I_{rr} = 0.25\text{ A}$		t_{rr}	20	ns
Maximum stored charge per diode	$I_F = 2\text{ A}$, $dI/dt = 20\text{ A}/\mu\text{s}$, $V_R = 30\text{ V}$, $I_{rr} = 0.1 I_{RM}$		Q_{rr}	9	nC

Note:

(1) Pulse test: 300 μs pulse width, 1 % duty cycle

THERMAL CHARACTERISTICS ($T_C = 25\text{ }^\circ\text{C}$ unless otherwise noted)					
PARAMETER	SYMBOL	UG10	UGF10	UGB10	UNIT
		BYQ28E	BYQ28EF	BYQ28EB	
Typical thermal resistance per diode, junction to ambient	$R_{\theta JA}$	50	55	50	$^\circ\text{C}/\text{W}$
Typical thermal resistance per diode, junction to case	$R_{\theta JC}$	4.5	6.7	4.8	

ORDERING INFORMATION (Example)					
PACKAGE	PREFERRED P/N	UNIT WEIGHT (g)	PACKAGE CODE	BASE QUANTITY	DELIVERY MODE
TO-220AB	BYQ28E-200-E3/45	1.80	45	50/tube	Tube
ITO-220AB	BYQ28EF-200-E3/45	1.95	45	50/tube	Tube
TO-263AB	BYQ28EB-200-E3/45	1.77	45	50/tube	Tube
TO-263AB	BYQ28EB-200-E3/81	1.77	81	800/reel	Tape reel
TO-220AB	BYQ28E-200HE3/45 ⁽¹⁾	1.80	45	50/tube	Tube
ITO-220AB	BYQ28EF-200HE3/45 ⁽¹⁾	1.95	45	50/tube	Tube
TO-263AB	BYQ28EB-200HE3/45 ⁽¹⁾	1.77	45	50/tube	Tube
TO-263AB	BYQ28EB-200HE3/81 ⁽¹⁾	1.77	81	800/reel	Tape reel

Note:

(1) Automotive grade AEC Q101 qualified



RATINGS AND CHARACTERISTICS CURVES

($T_A = 25\text{ }^\circ\text{C}$ unless otherwise noted)

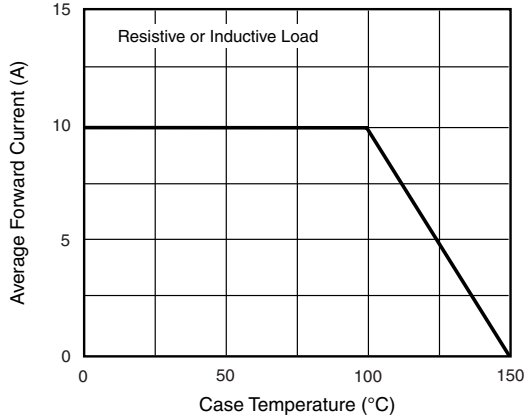


Figure 1. Forward Current Derating Curve

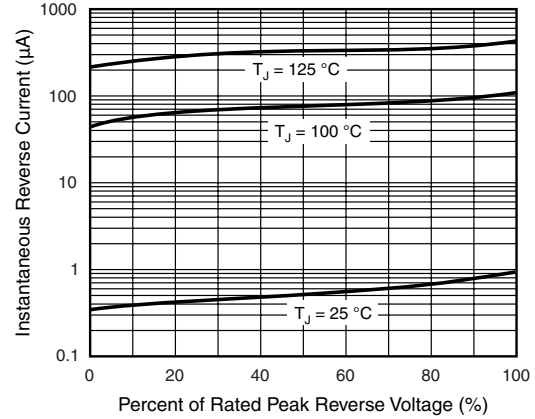


Figure 4. Typical Reverse Characteristics Per Diode

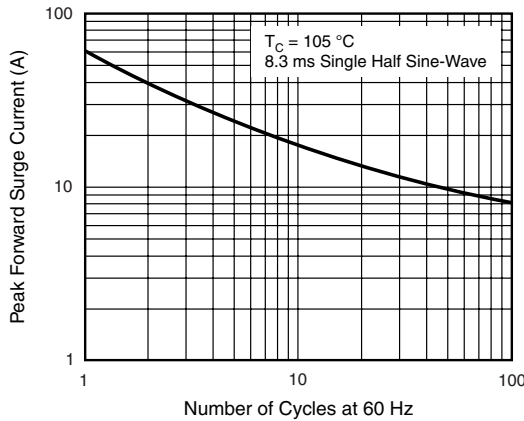


Figure 2. Maximum Non-Repetitive Peak Forward Surge Current Per Diode

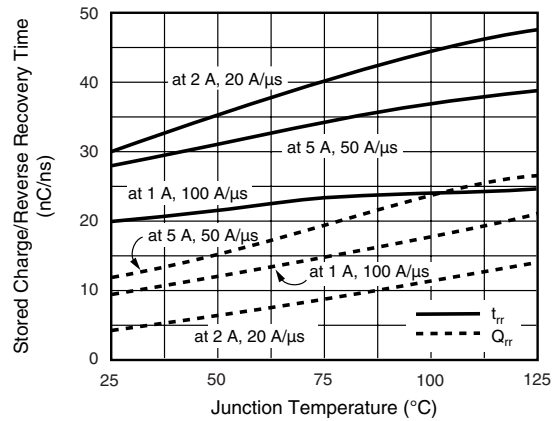


Figure 5. Reverse Switching Characteristics Per Diode

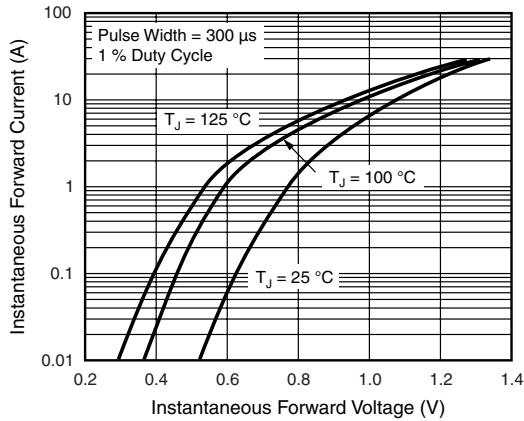


Figure 3. Typical Instantaneous Forward Characteristics Per Diode

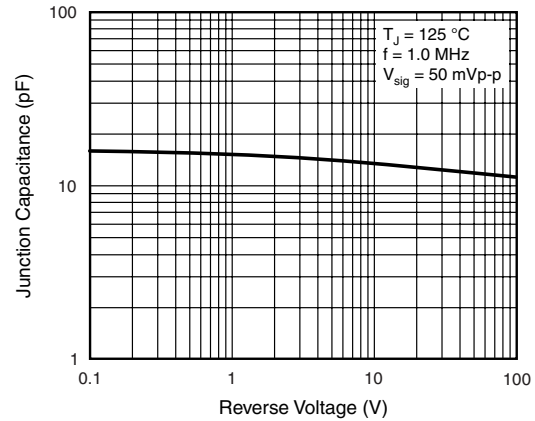


Figure 6. Typical Junction Capacitance Per Diode

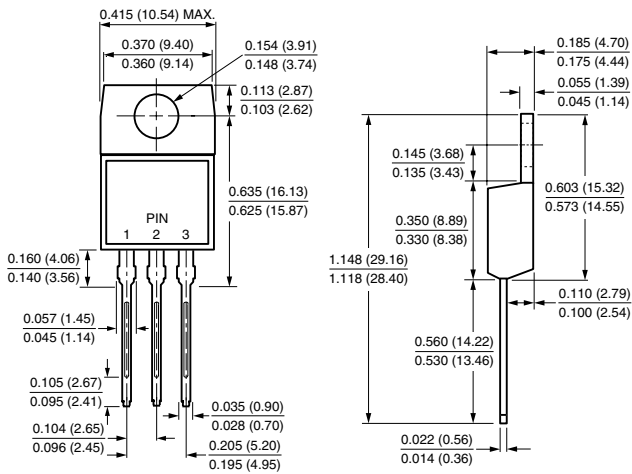
BYQ28E(F,B)-100 thru BYQ28E(F,B)-200, UG(F,B)10BCT

Vishay General Semiconductor

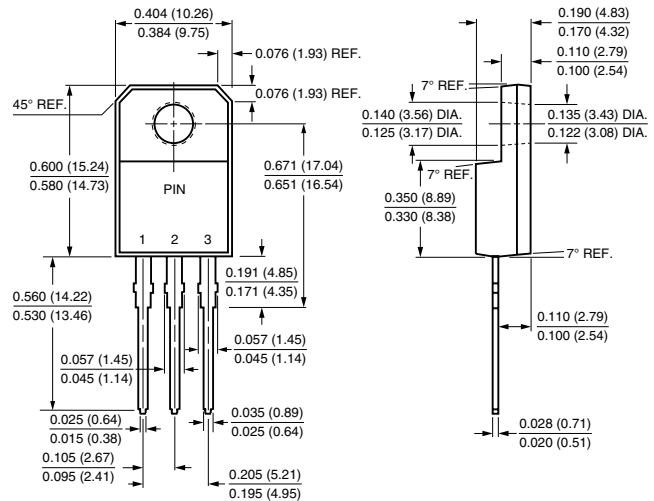


PACKAGE OUTLINE DIMENSIONS in inches (millimeters)

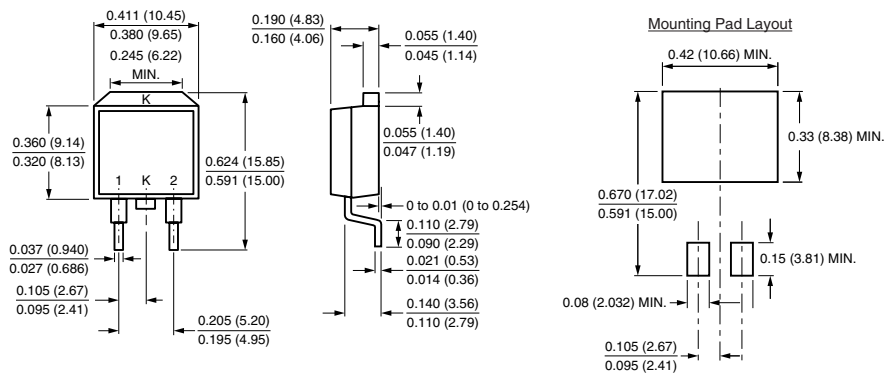
TO-220AB



ITO-220AB



TO-263AB





Notice

Specifications of the products displayed herein are subject to change without notice. Vishay Intertechnology, Inc., or anyone on its behalf, assumes no responsibility or liability for any errors or inaccuracies.

Information contained herein is intended to provide a product description only. No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document. Except as provided in Vishay's terms and conditions of sale for such products, Vishay assumes no liability whatsoever, and disclaims any express or implied warranty, relating to sale and/or use of Vishay products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright, or other intellectual property right.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Vishay for any damages resulting from such improper use or sale.